

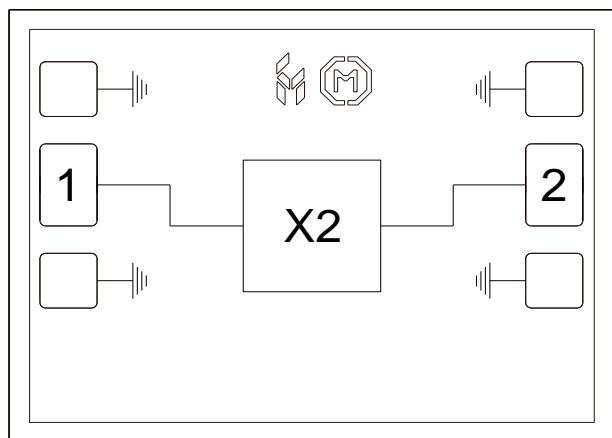
### Product Overview

The CMD226 die is a broadband MMIC GaAs x2 passive frequency multiplier. When driven by a +15 dBm signal, the multiplier provides 10.5 dB conversion loss at an output frequency of 18 GHz. The Fo and 3Fo isolations are 44 dBc and 46 dBc respectively. The CMD226 is a 50 ohm matched design eliminating the need for RF port matching.

### Key Features

- Low Conversion Loss
- Excellent Fo Isolation
- Broadband Performance
- No Bias Required
- Small Die Size: 1060 um x 790 um

### Functional Block Diagram



### Ordering Information

| Part No. | Description   |
|----------|---|
| CMD226   | Passive Frequency Doubler, 7-11 GHz Input, 100 Piece Gel Pack |

### Electrical Performance ( $T_A = 25^\circ\text{C}$ , $P_{in} = +15\text{ dBm}$ , $F_{in} = 9\text{ GHz}$ )

| Parameter                                   | Min | Typ     | Max | Units |
|---|-----|---------|-----|-------|
| Frequency Range, Input                      |     | 7 - 11  |     | GHz   |
| Frequency Range, Output                     |     | 14 - 22 |     | GHz   |
| Conversion Loss                             |     | 10.5    |     | dB    |
| Fo Isolation (with respect to input level)  |     | 44      |     | dB    |
| 3Fo Isolation (with respect to input level) |     | 46      |     | dB    |
| 4Fo Isolation (with respect to input level) |     | 50      |     | dB    |

## Absolute Maximum Ratings

| Parameter                         | Rating        |
|-----------------------------------|---------------|
| RF Input Power                    | +22 dBm       |
| Operating Temperature             | -55 to 85 °C  |
| Storage Temperature               | -55 to 150 °C |
| Thermal Resistance, $\theta_{JC}$ | 605 °C/W      |

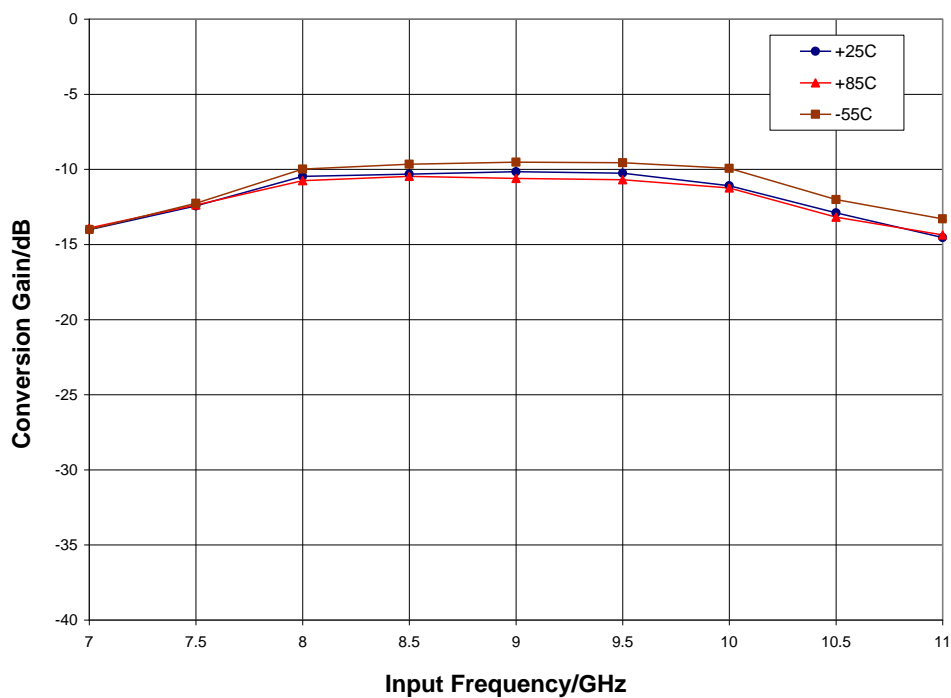
Exceeding any one or combination of the maximum ratings may cause permanent damage to the device.

## Electrical Specifications ( $T_A = 25\text{ °C}$ , $P_{in} = +15\text{ dBm}$ )

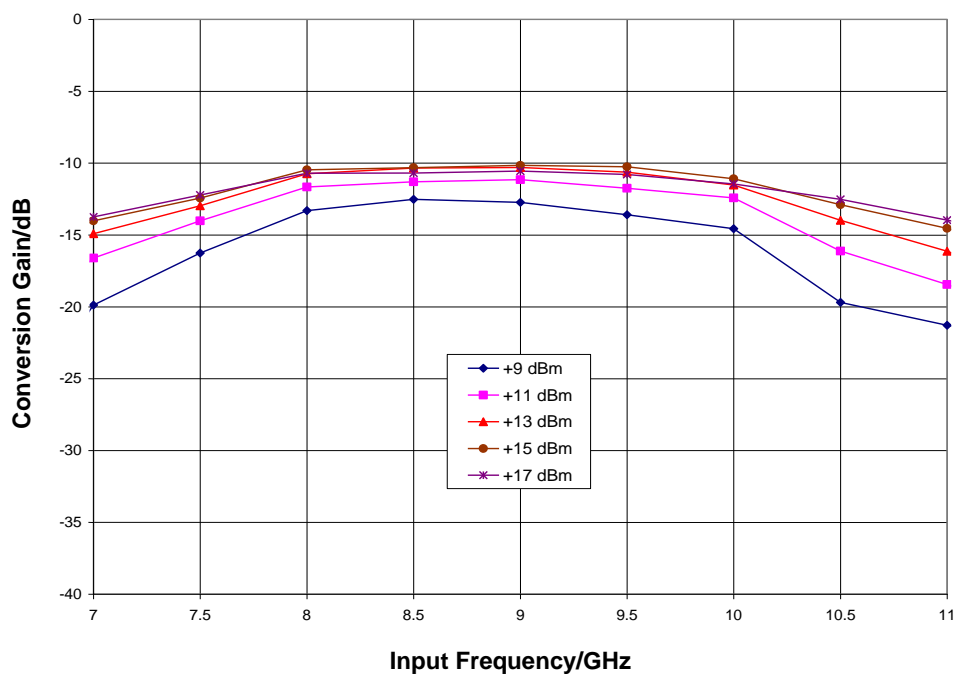
| Parameter                                   | Min     | Typ | Max | Min     | Typ  | Max | Units |
|---|---------|-----|-----|---------|------|-----|-------|
| Frequency Range, Input                      | 7 - 11  |     |     | 8 - 10  |      |     | GHz   |
| Frequency Range, Output                     | 14 - 22 |     |     | 16 - 20 |      |     | GHz   |
| Conversion Loss                             |         | 11  | 16  |         | 10.5 | 13  | dB    |
| Fo Isolation (with respect to input level)  | 33      | 44  |     | 33      | 44   |     | dB    |
| 3Fo Isolation (with respect to input level) | 37      | 48  |     | 40      | 48   |     | dB    |
| 4Fo Isolation (with respect to input level) | 25      | 45  |     | 33      | 45   |     | dB    |

## Typical Performance

Conversion Gain vs. Temperature @ +15 dBm Drive Level

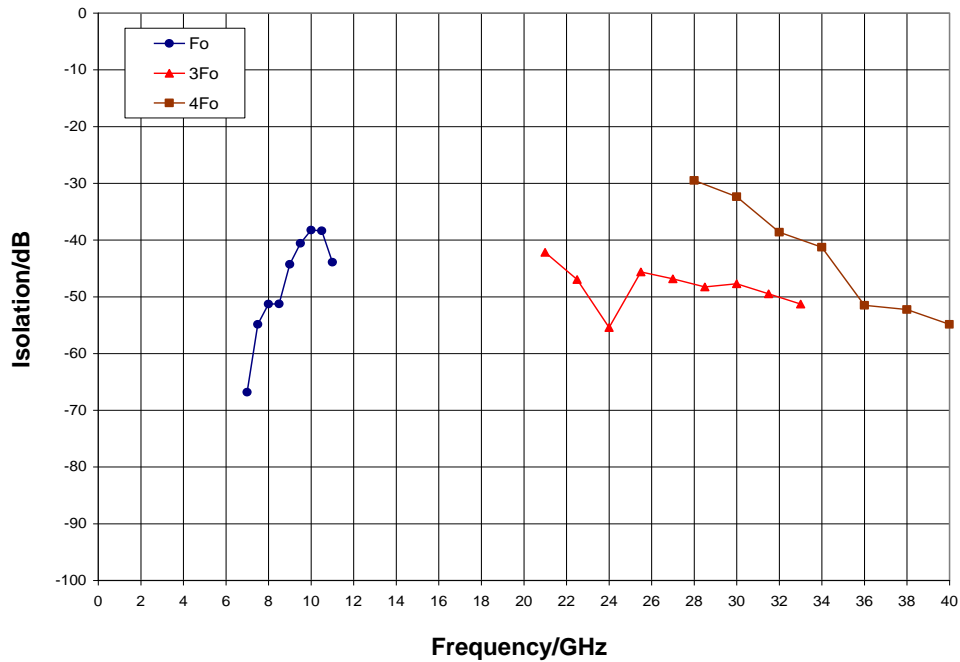


Conversion Gain vs. Drive Level,  $T_A = 25^\circ\text{C}$

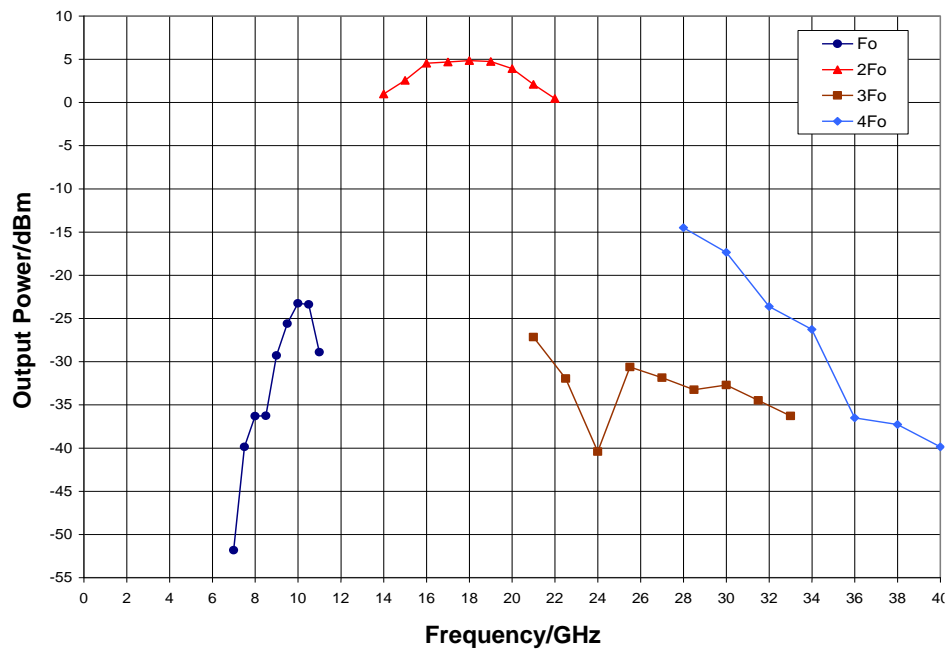


## Typical Performance

Isolation (with respect to input level) @ +15 dBm Drive Level,  $T_A = 25^\circ\text{C}$

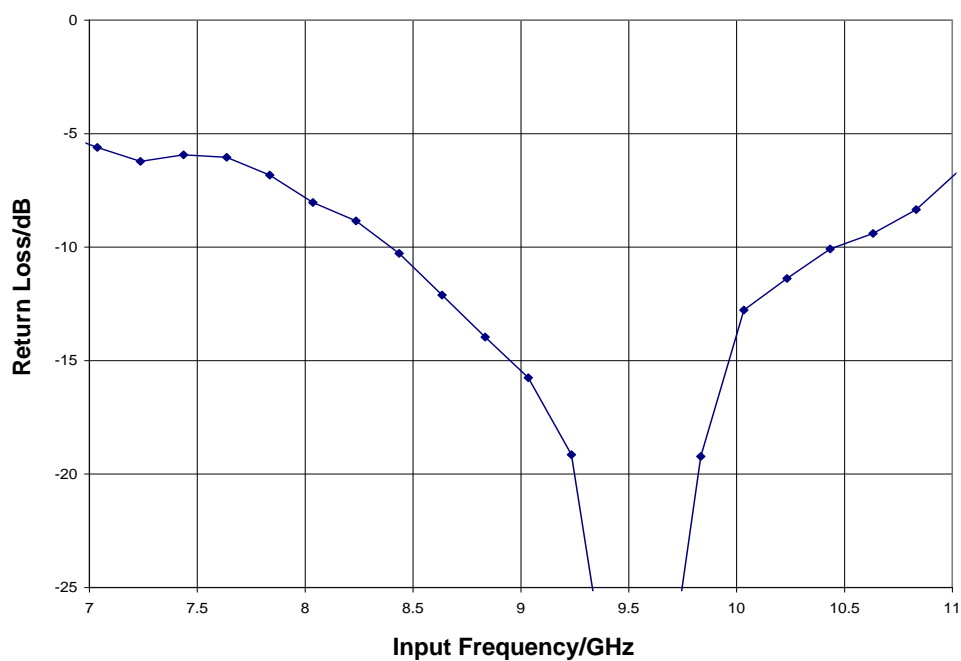


Output Spectrum @ +15 dBm Drive Level,  $T_A = 25^\circ\text{C}$

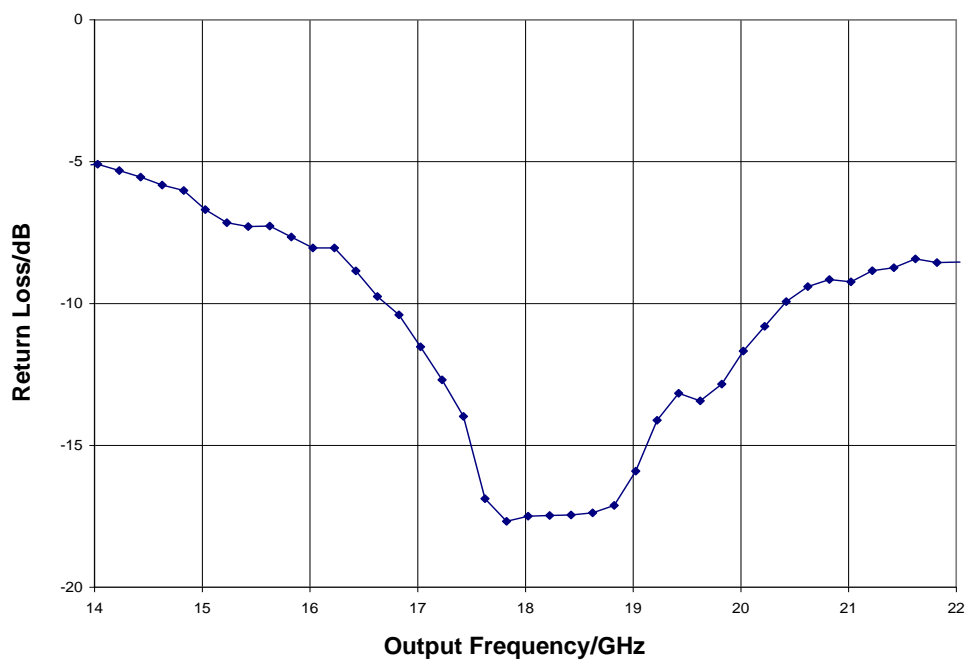


## Typical Performance

Input Return Loss @ +15 dBm Drive Level,  $T_A = 25^\circ\text{C}$

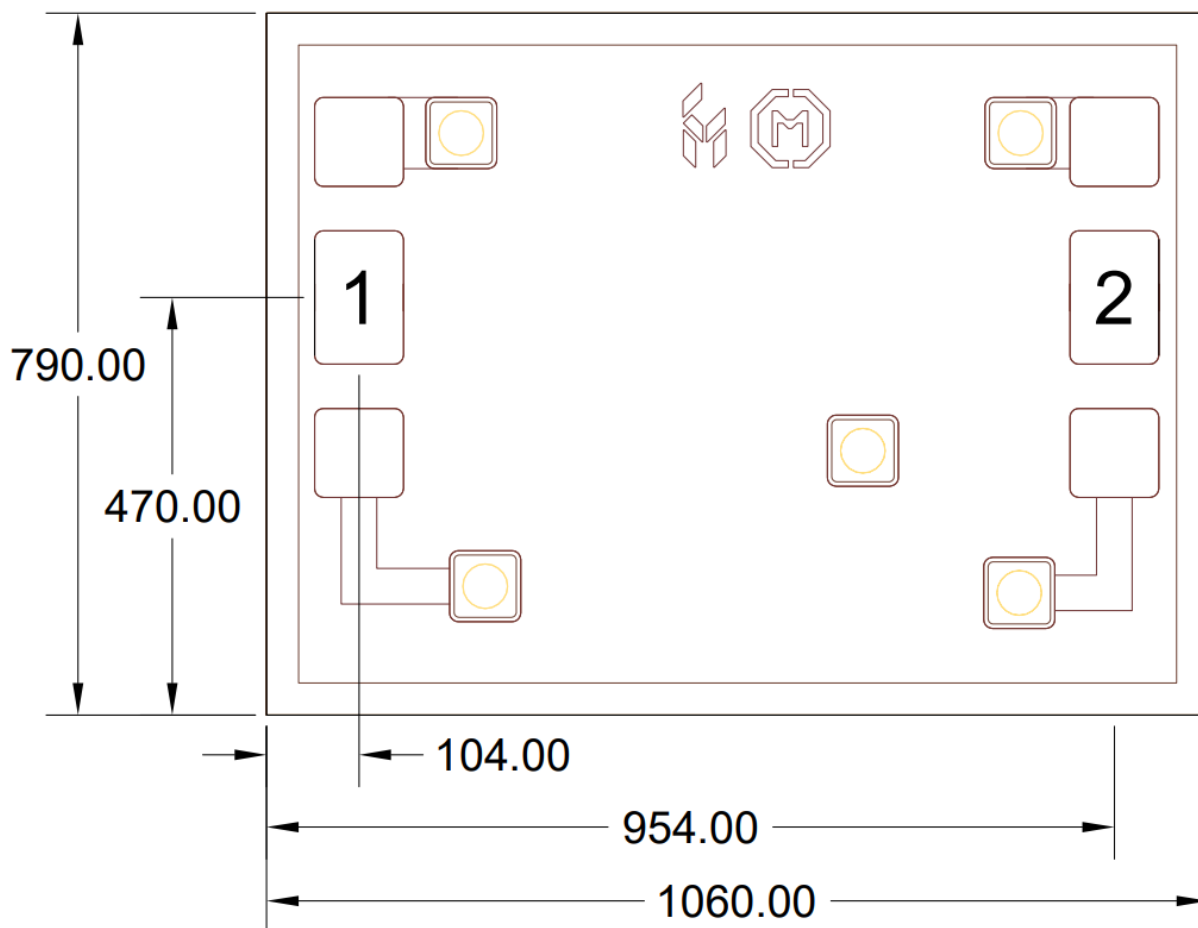


Output Return Loss @ +15 dBm Drive Level,  $F = 9\text{ GHz}$  Input,  $T_A = 25^\circ\text{C}$



## Mechanical Information

Die Outline (all dimensions in microns)

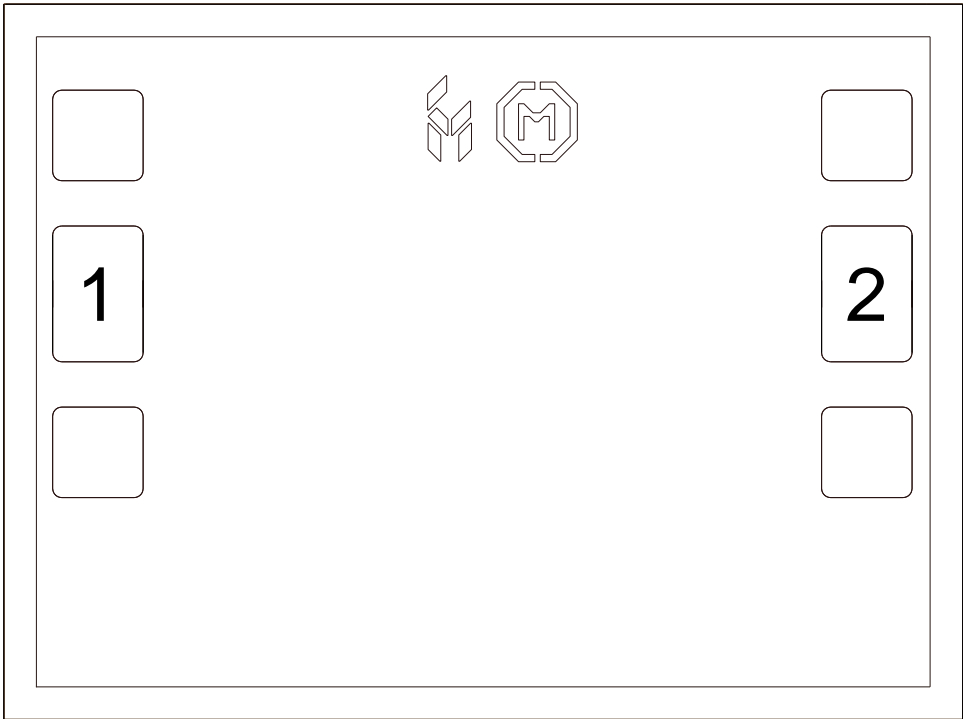


**Notes:**

1. No connection required for unlabeled pads
2. Backside is RF and DC ground
3. Backside and bond pad metal: Gold
4. Die is 100 microns thick
5. RF bond pads (1, 2) are 100 x 150 microns

Pin Description

Pad Diagram



Functional Description

| Pad      | Function | Description                          | Schematic |
|----------|----------|--------------------------------------|-----------|
| 1        | RF in    | Pad is DC coupled and 50 ohm matched |           |
| 2        | RF out   | Pad is DC coupled and 50 ohm matched |           |
| Backside | Ground   | Connect to RF / DC ground            |           |

## Applications Information

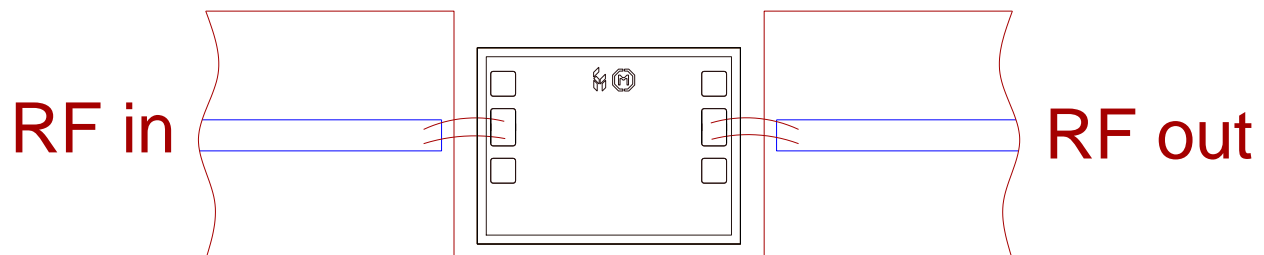
### Assembly Guidelines

The backside of the CMD226 is RF ground. Die attach should be accomplished with electrically and thermally conductive epoxy. Eutectic attach is not recommended. Standard assembly procedures should be followed for high frequency devices. The top surface of the semiconductor should be made planar to the adjacent RF transmission lines.

RF connections should be made as short as possible to reduce the inductive effect of the bond wire. Use of a 0.8 mil thermosonic wedge bonding is highly recommended as the loop height will be minimized. The RF input and output require double bond wires as shown.

The semiconductor is 100 um thick and should be handled by the sides of the die or with a custom collet. Do not make contact directly with the die surface as this will damage the monolithic circuitry. Handle with care.

### Assembly Diagram



**GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.**



## Handling Precautions

| Parameter                    | Rating   | Standard                 |
|------------------------------|----------|--------------------------|
| ESD – Human Body Model (HBM) | Class 1A | ESDA / JEDEC JS-001-2012 |



Caution!  
ESD-Sensitive Device

## RoHS Compliance

This part is compliant with 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment) as amended by Directive 2015/863/EU.

This product also has the following attributes:

- Lead Free
- Antimony Free
- TBBP-A (C<sub>15</sub>H<sub>12</sub>Br<sub>4</sub>O<sub>2</sub>) Free
- SVHC Free
- Halogen Free
- PFOS Free

## Contact Information

For the latest specifications, additional product information, worldwide sales and distribution locations:

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